

Insulated Gate Bipolar Transistor, IGBT

360V, 50A High Speed Punch Through IGBT

Features

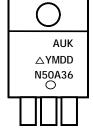
- Low gate charge
- Punch Through Technology
- Low saturation voltage: $V_{CE(sat)} = 1.6V$ (@ IC = 50A, TC = 25°C)
- RoHS compliant product

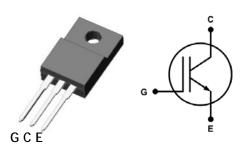
Applications

- General purpose inverters
- PDP
- UPS

Ordering Information

Part Number	Marking	Package	
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SGTN50A36FD	N50A36	TO-220F	ļ





TO-220F-3L

Column 1: Manufacturer Column 2: Production Information e.g.) △YMDD

- -. △: Factory Management Code
 -. YMDD: Date Code (Year, Month, Date)
- Column 3: Device Code

Absolute maximum ratings (Tc=25°C unless otherwise noted)

Characteristic	Symbol		Rating	Unit
Collector-emitter voltage	V _{CES}		V _{CES} 360	
Continuous collector current (1)	۱ _с	T _c =25°C	100	А
		T _c =100°C	50	А
Pulsed collector current ⁽²⁾	I _{CM}		I _{CM} 240	
Gate-emitter voltage	e-emitter voltage V _{GES}		±30	V
Turn-off safe area	fe area -		200	А
Power dissipation		P _D	30	W
Operating and storage temperature range	T _{J,} T _{stg}		-55 to 150	°C
Maximum lead temperature for soldering purpose		TL	300	°C

¹⁾ Collector current limited by maximum junction temperature

²⁾ Pulse width limited by maximum junction temperature and turn-off within RBSOA.

Thermal Characteristics

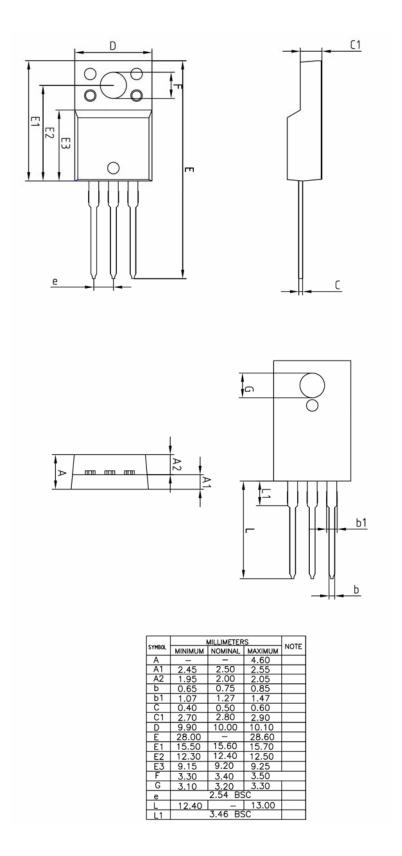
Characteristic	Symbol	Rating	Unit	
Thermal resistance, junction to case	R _{th(j-c)}	Max. 4.16		
Thermal resistance, junction to ambient	$R_{th(j-a)}$	Max. 62.5	°C/W	

Electrical Characteristics (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Off-Characteristics						
Collector-emitter breakdown voltage	BV _{CES}	I _C =500uA, V _{GS} =0	360	-	-	V
Breakdown voltage temperature coefficient	△BV _{CES} /△T」	I_{c} =1mA, reference to 25°C	-	0.5	-	V/°C
Zero gate voltage collector current	I _{CES}	V_{CE} =360V, V_{GS} =0V, T_{C} =25°C	-	-	10	uA
Gate-body leakage current	I _{GSS}	$V_{DS}=0V$, $V_{GS}=\pm 30V$	-	-	±400	nA
On-Characteristics						
Gate threshold voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}$, $I_C=250uA$	2	-	4.5	V
Collector-emitter saturation voltage	V _{CE(sat)}	V _{GE} =15V, I _C =35A	-	1.4	1.6	V
		V _{GE} =15V, I _C =50A	-	1.6	1.8	V
Dynamic-Characteristics		·				
Input capacitance	C _{ies}		-	1500	-	pF
Output capacitance	C _{oes}	V _{CE} =25V, V _{GE} =0V, f=1MHz	-	100	-	
Reverse transfer capacitance	C _{res}		-	50	-	
Turn-on delay time ^{(3),(4)}	t _{d(on)}		-	30	-	
Rise time ^{(3),(4)}	t _r	− V _{CE} =200V, I _C =35A,	-	100	-	ns
Turn-off delay time ^{(3),(4)}	t _{d(off)}	$R_{G}=5\Omega$	-	100	-	
Fall time ^{(3), (4)}	t _f	1	-	150	-	
Total gate charge ^{(3),(4)}	Q		-	67	-	nC
Gate-emitter charge ^{(3),(4)}	Q _{ge}	V _{CE} =150V, V _{GE} =15V, I _C =35A	-	11.7	-	
Gate-collector charge ^{(3),(4)}	Q _{gs}		-	23.5	-	

³⁾ Pulse test: Pulse width≤300us, Duty cycle≤2%
 ⁴⁾ Essentially independent of operating temperature typical characteristics

Package Outline Dimensions



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